

The background of the slide features a light gray circuit board pattern with various traces and circular components. A solid dark gray horizontal band runs across the middle of the image, serving as a background for the text.

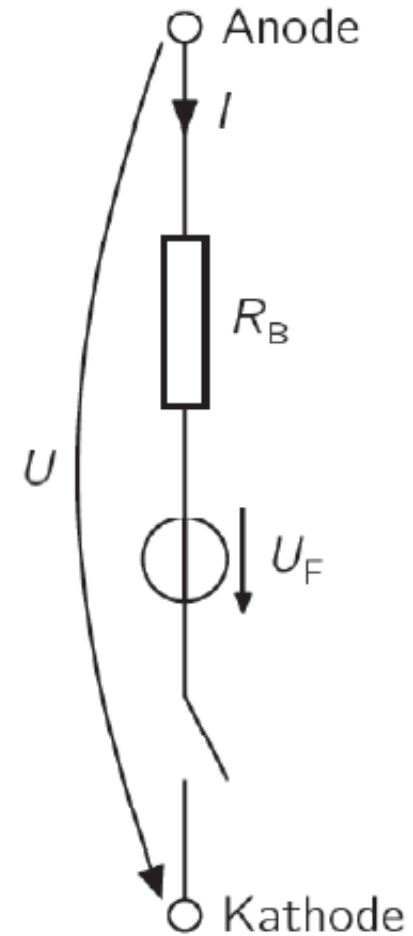
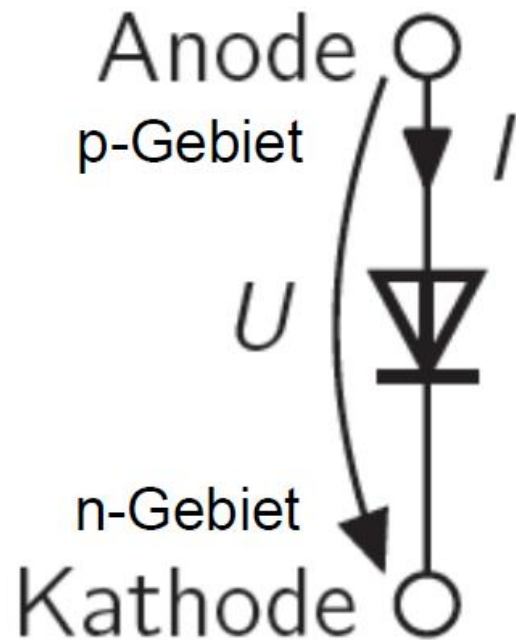
Diode

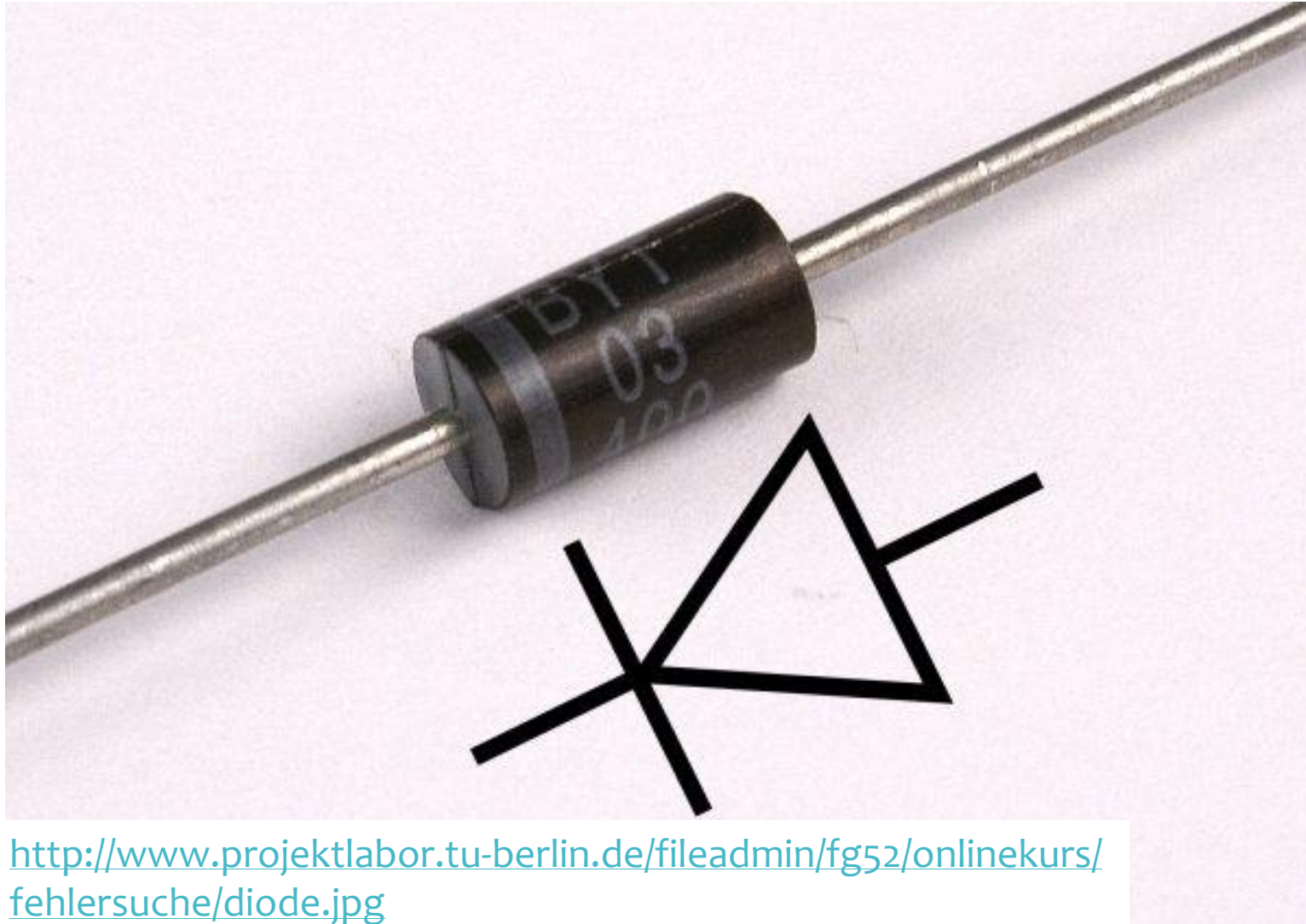
Aufbau, Eigenschaften & Verwendung

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Schaltzeichen & Ersatzschaltbild





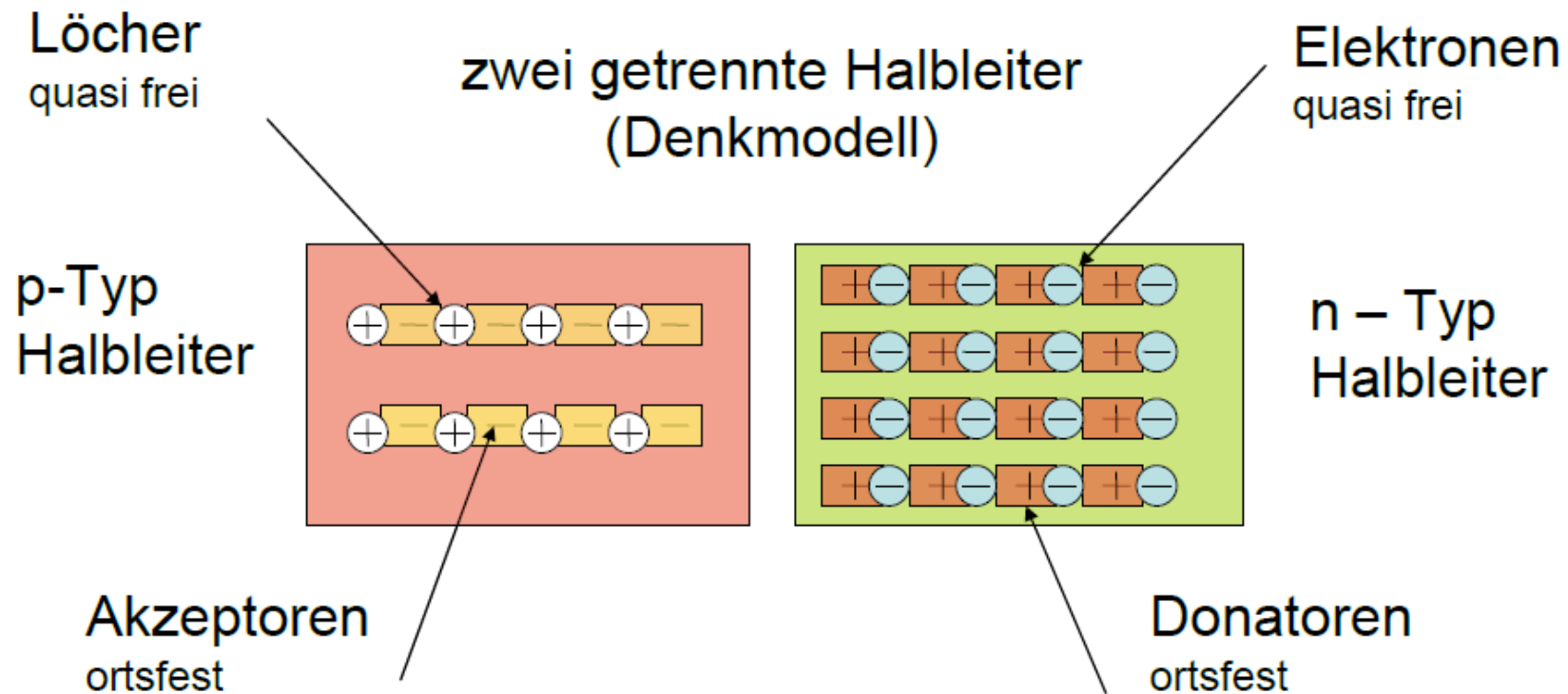
<http://www.projektlabor.tu-berlin.de/fileadmin/fg52/onlinekurs/fehlersuche/diode.jpg>

Anwendungsgebiete

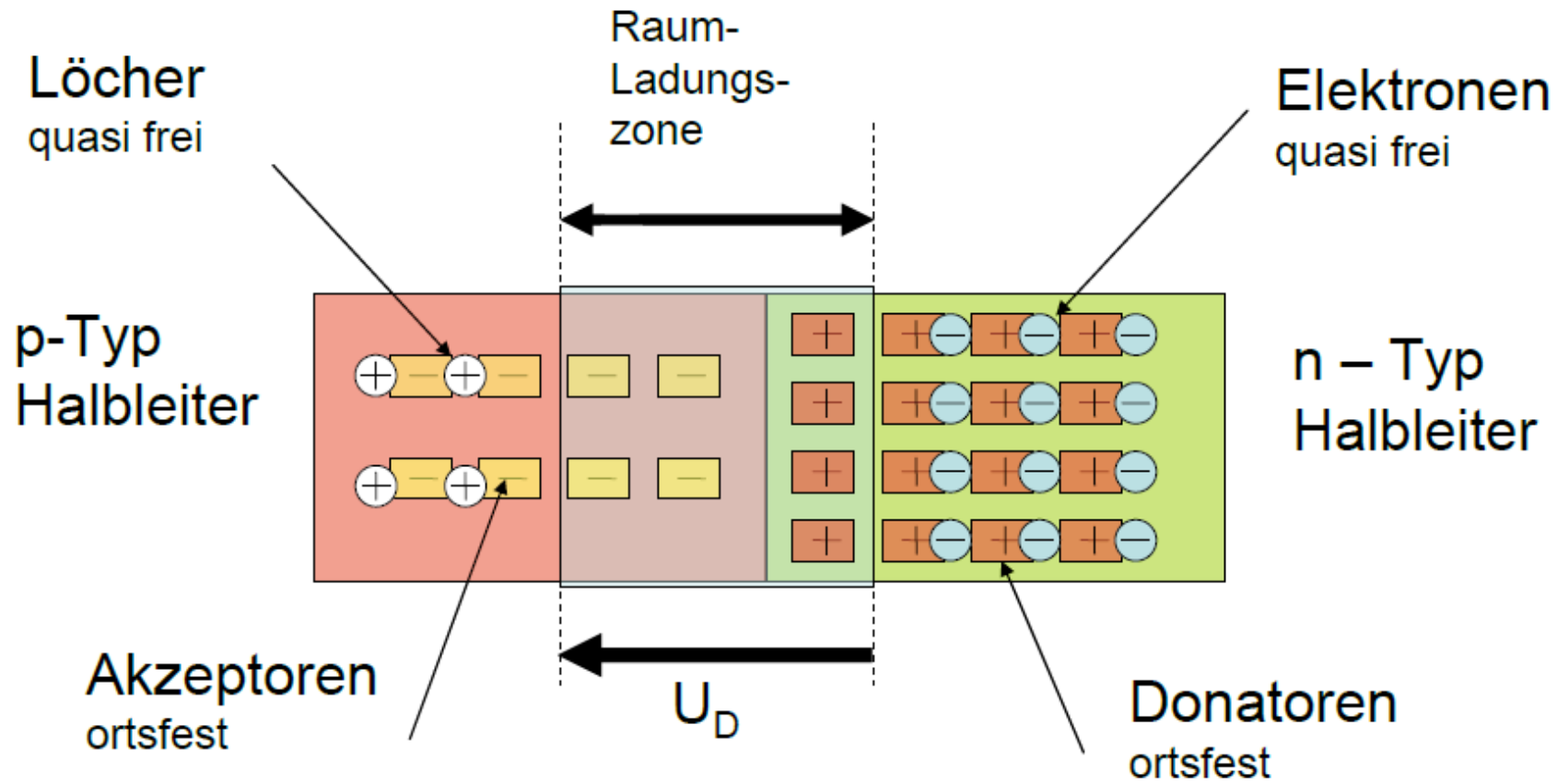
- Gleichrichter
- Verpolungsschutz
- Spannungsstabilisierung (Zener-Diode)
- Abstimmung von Schwingkreisen (Kapazitätsdiode)
- Erzeugung sichtbares Licht (LED)

Aufbau

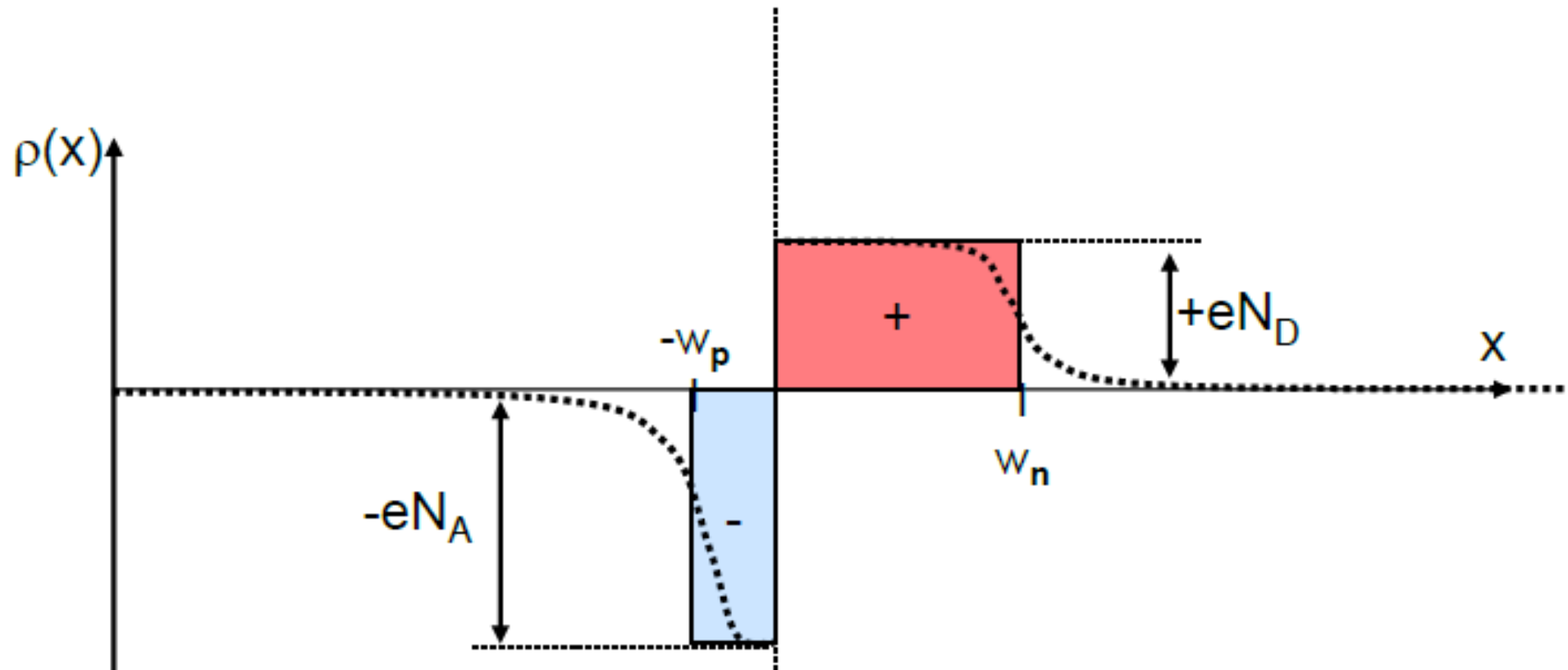
- zwei unterschiedliche Dotierungszonen (p- & n-Gebiet), deren Enden mit metallischen Kontakten versehen sind

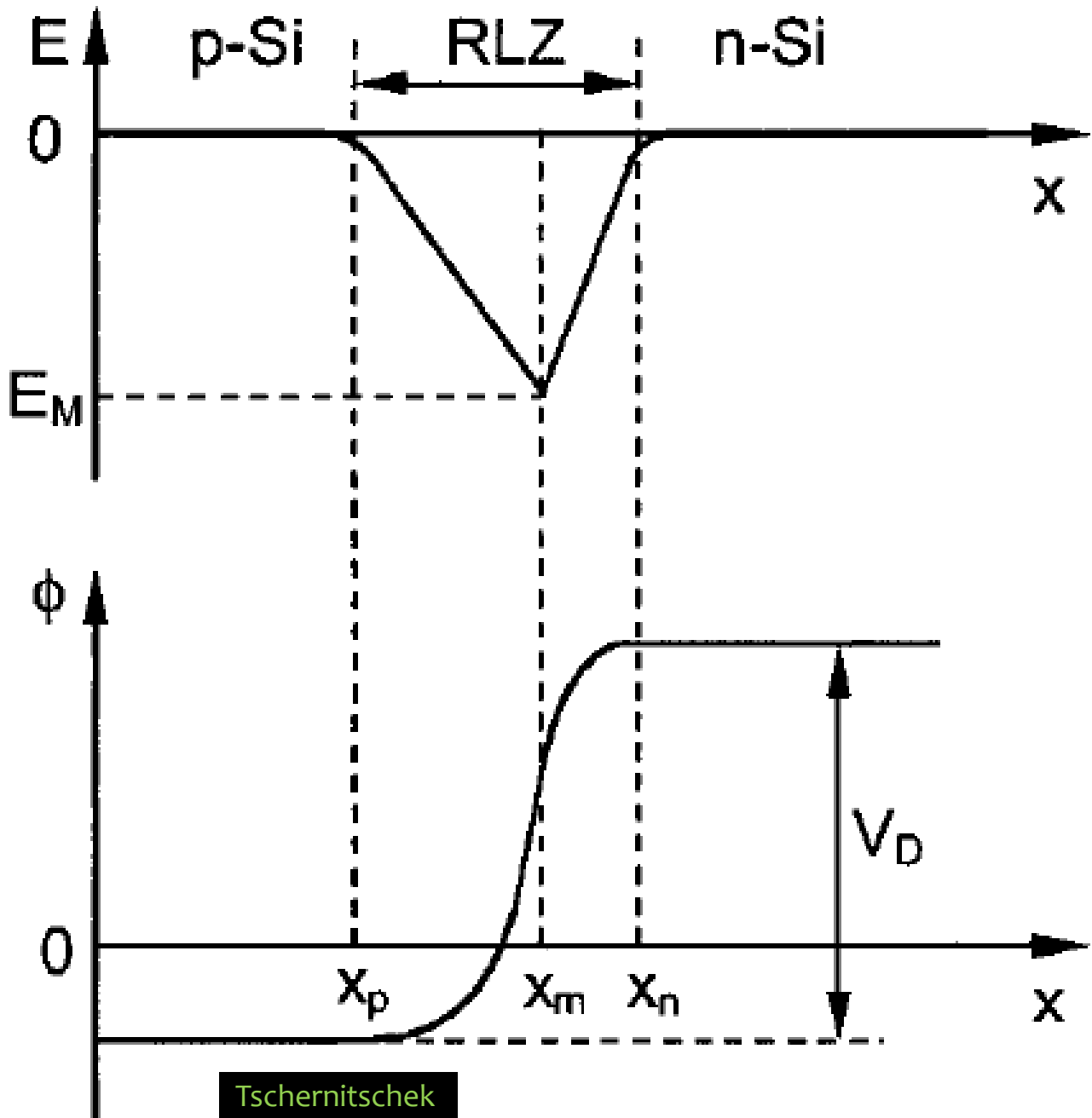


Aufbau



Aufbau





Tschernitschek

$$E(-x_p \leq x < 0) = \int_{x=-x_p}^x \frac{-eN_A}{\epsilon} dx$$

$$= -\frac{eN_A(x + x_p)}{\epsilon}$$

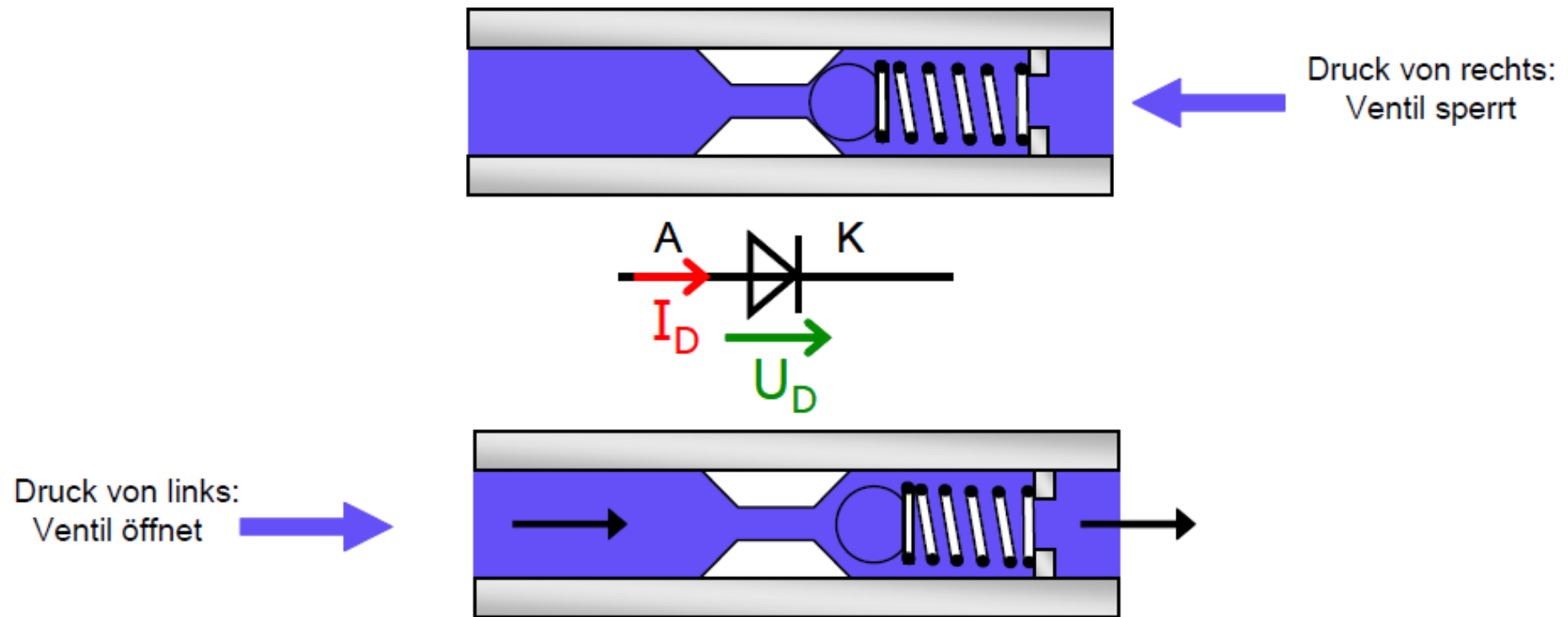
$$E(x = 0) = -\frac{eN_A x_p}{\epsilon}$$

$$E(0 < x \leq x_n) = \int_x^{x=x_n} \frac{eN_D}{\epsilon} dx$$

$$= \frac{eN_D x_n}{\epsilon}$$

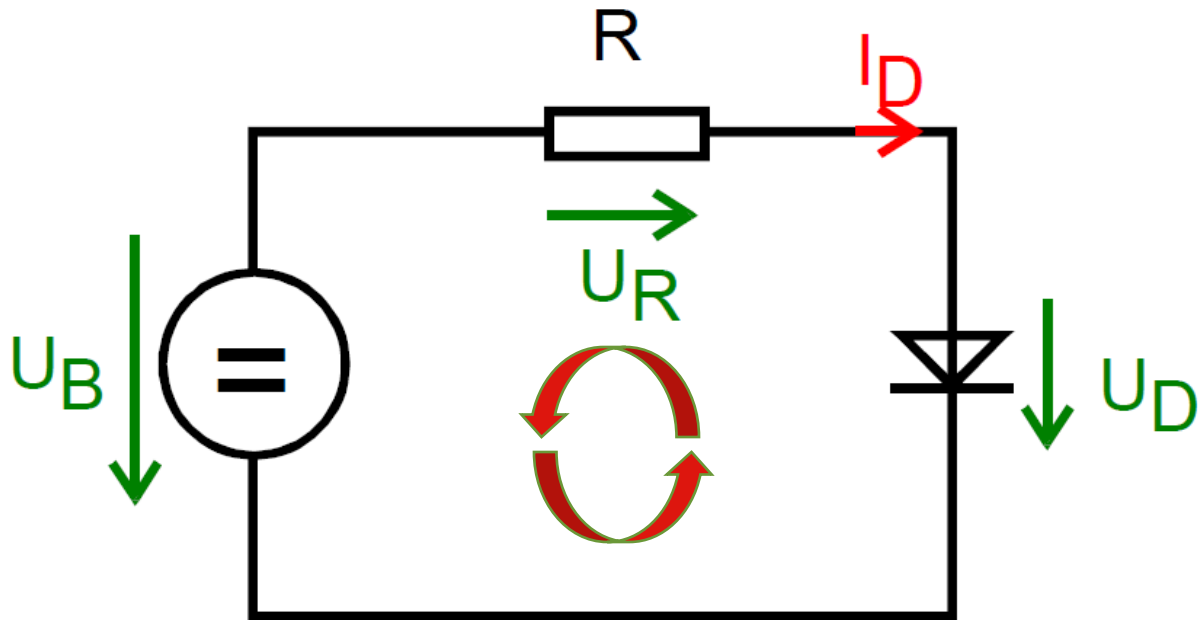
$$\vec{E} = -grad(\Phi) \longrightarrow \Phi = - \int_{-x_p}^{+x_n} \vec{E} \cdot d\vec{x}$$

Hydraulisches Äquivalent



Diodenkennlinie

- Herleitung idealisierte Kennlinie:

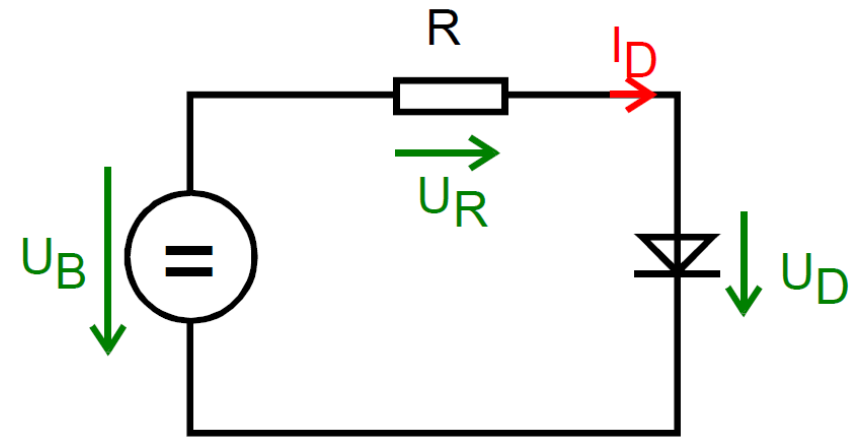
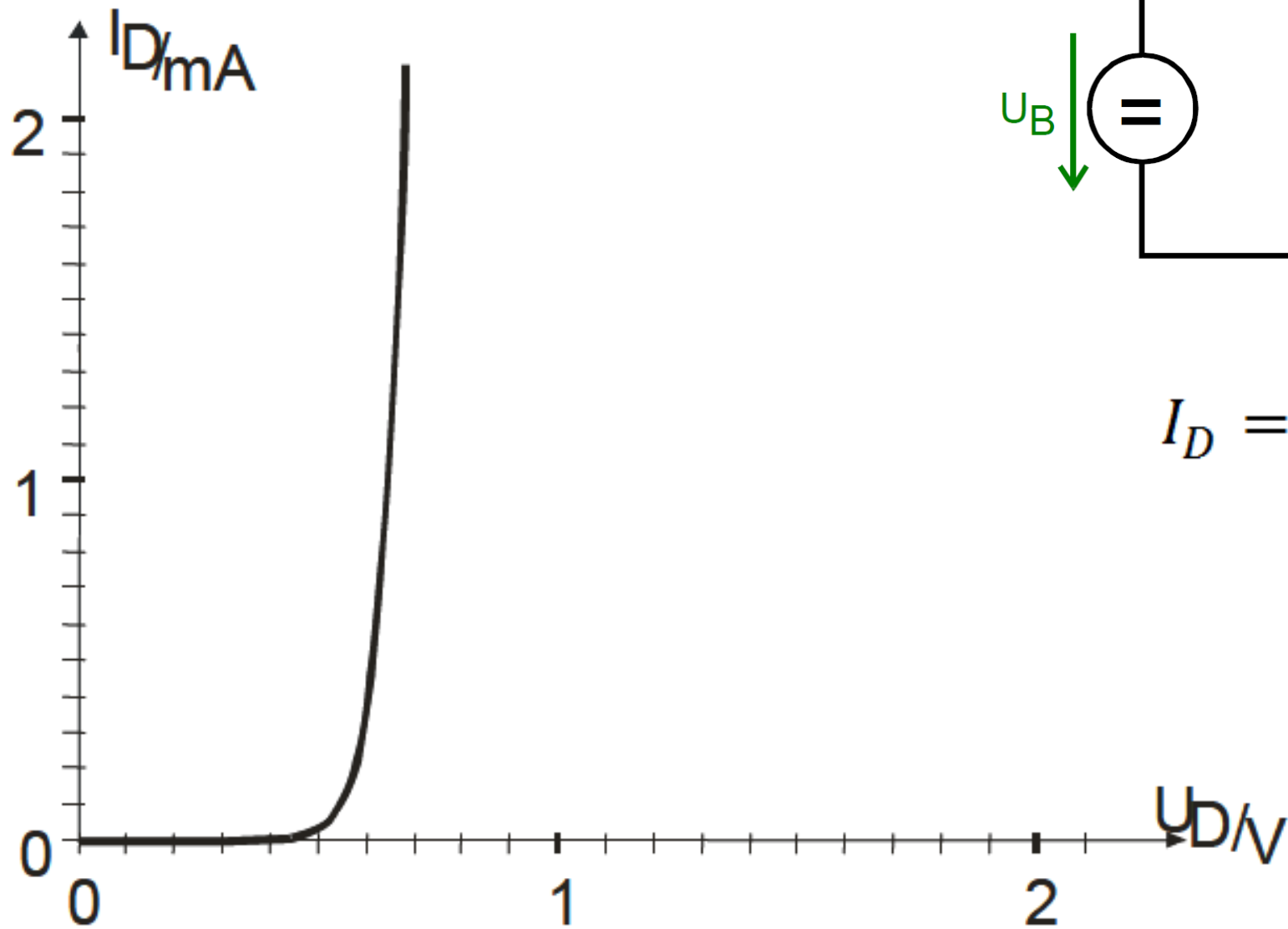


$$U_B = 2V, R = 1k\Omega$$

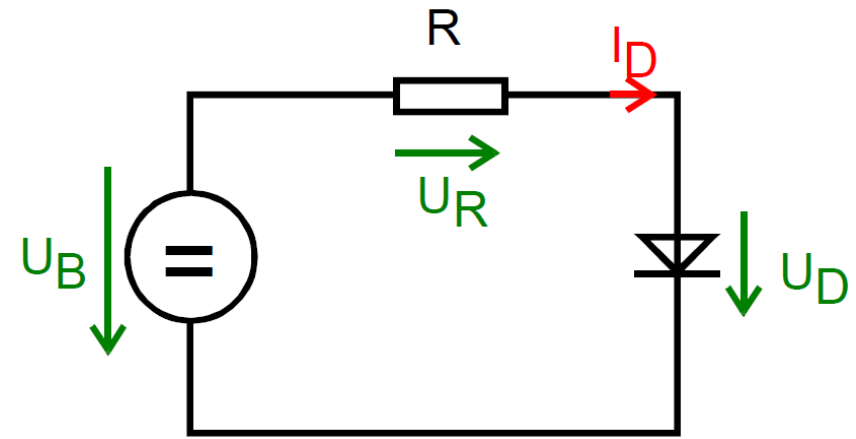
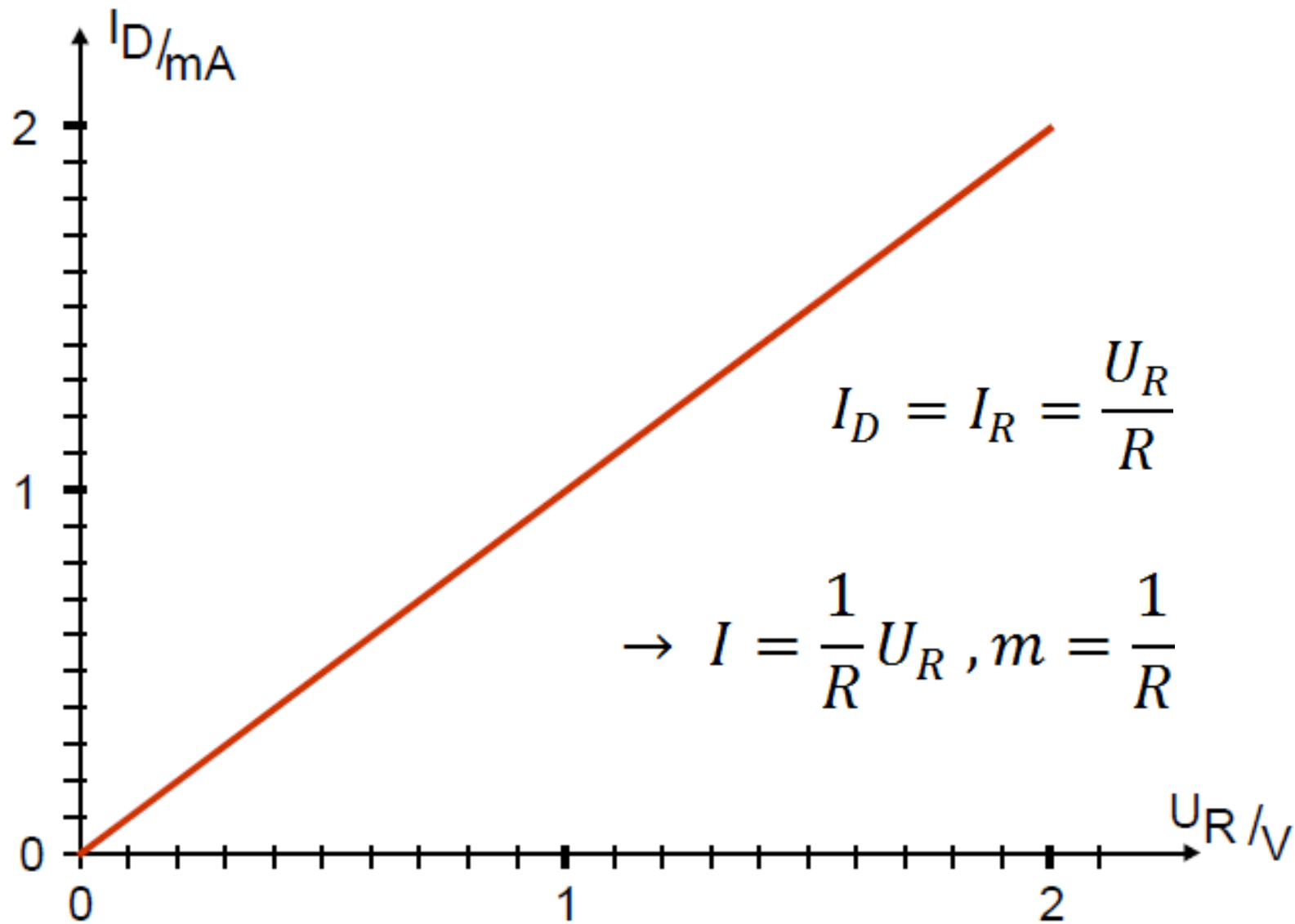
$$\sum U = 0 = U_B - U_D - U_R$$

$$\rightarrow U_D = U_B - U_R$$

$$\rightarrow U_R = U_B - U_D$$

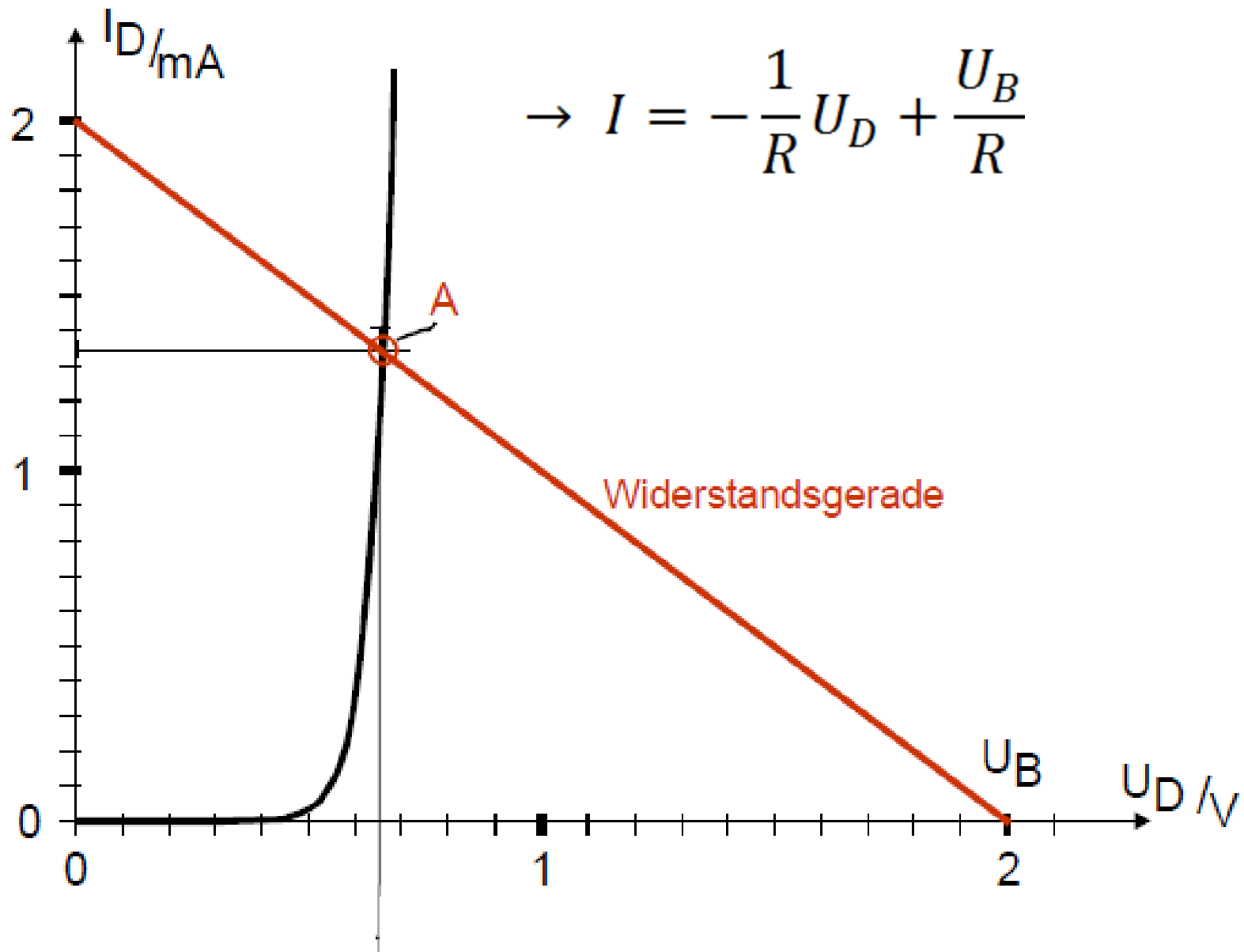


$$I_D = I_R = \frac{U_R}{R}$$

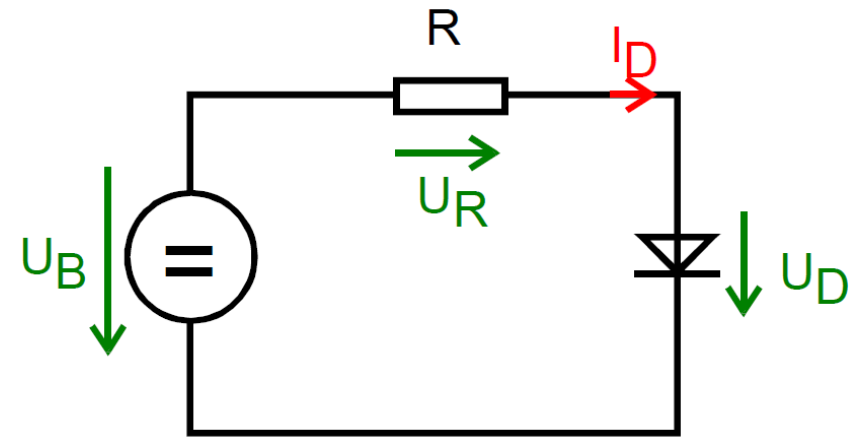


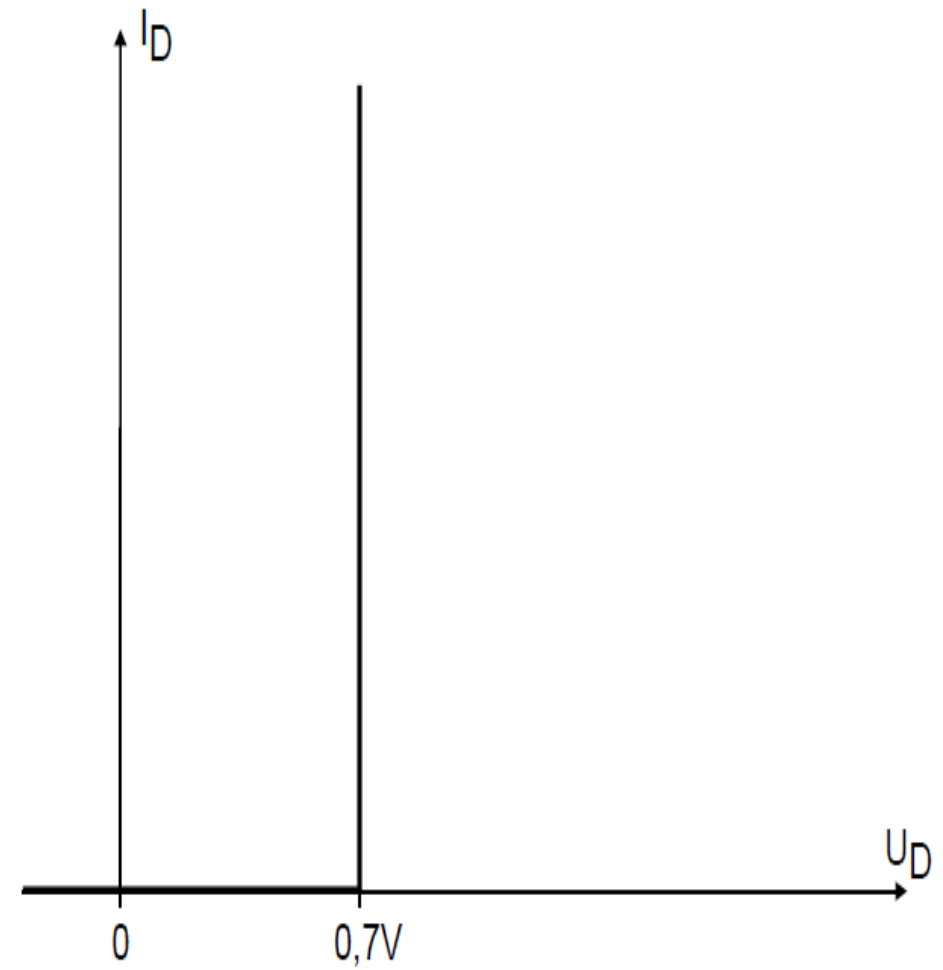
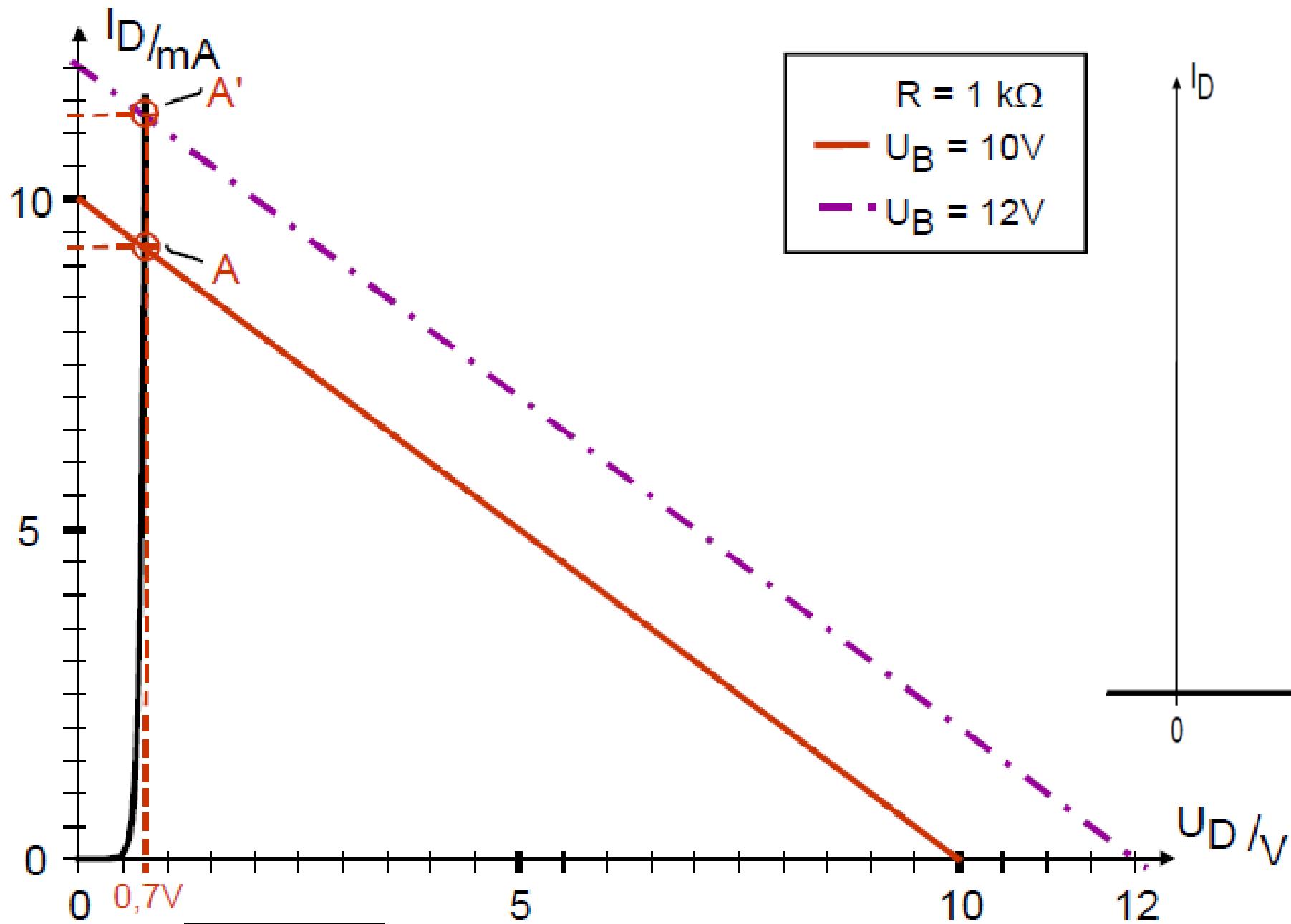
$$I = \frac{U_R}{R} = \frac{U_B - U_D}{R}$$

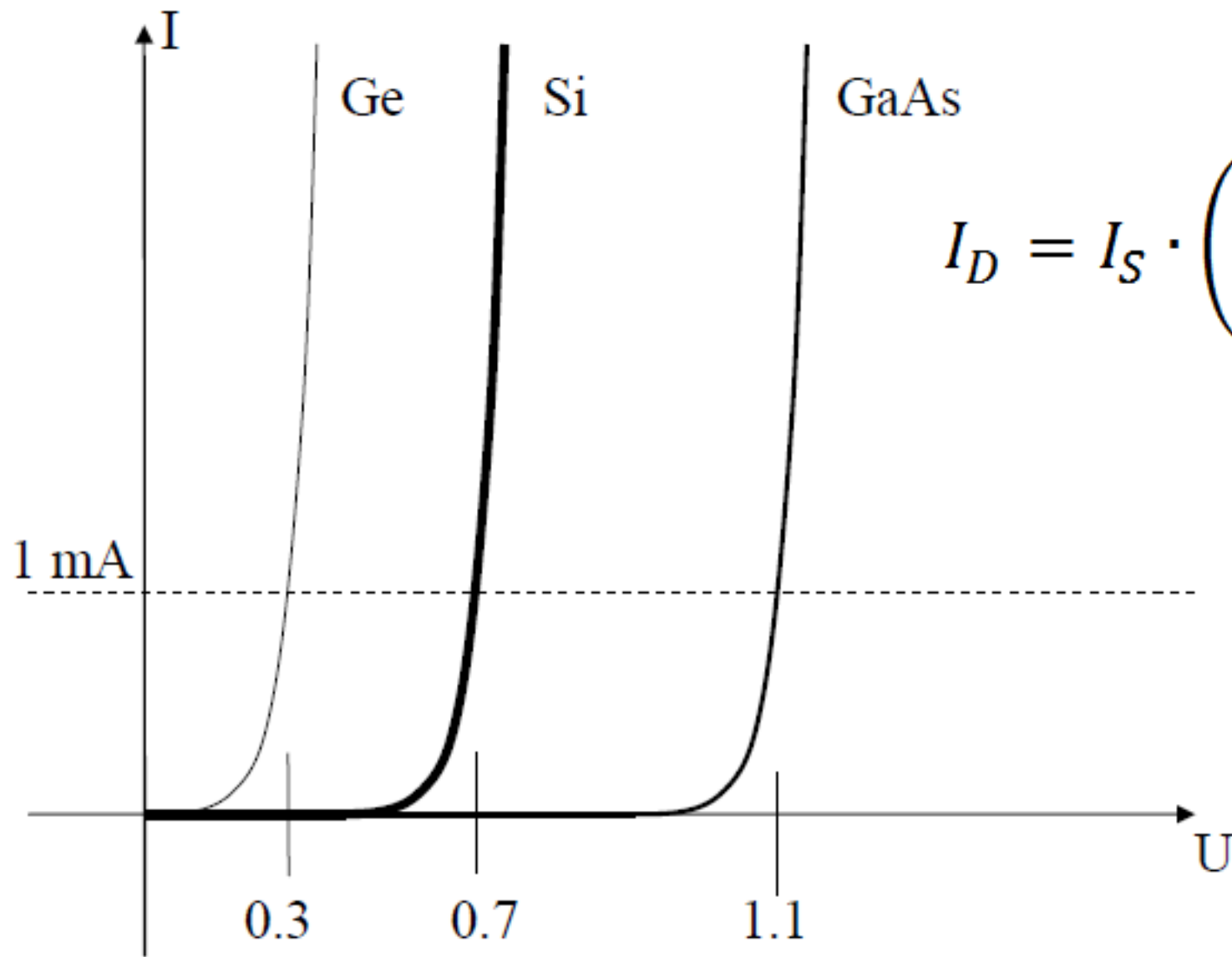
$$\rightarrow I = -\frac{1}{R} U_D + \frac{U_B}{R}$$



$$\rightarrow I = -\frac{1}{R} U_D + \frac{U_B}{R}$$

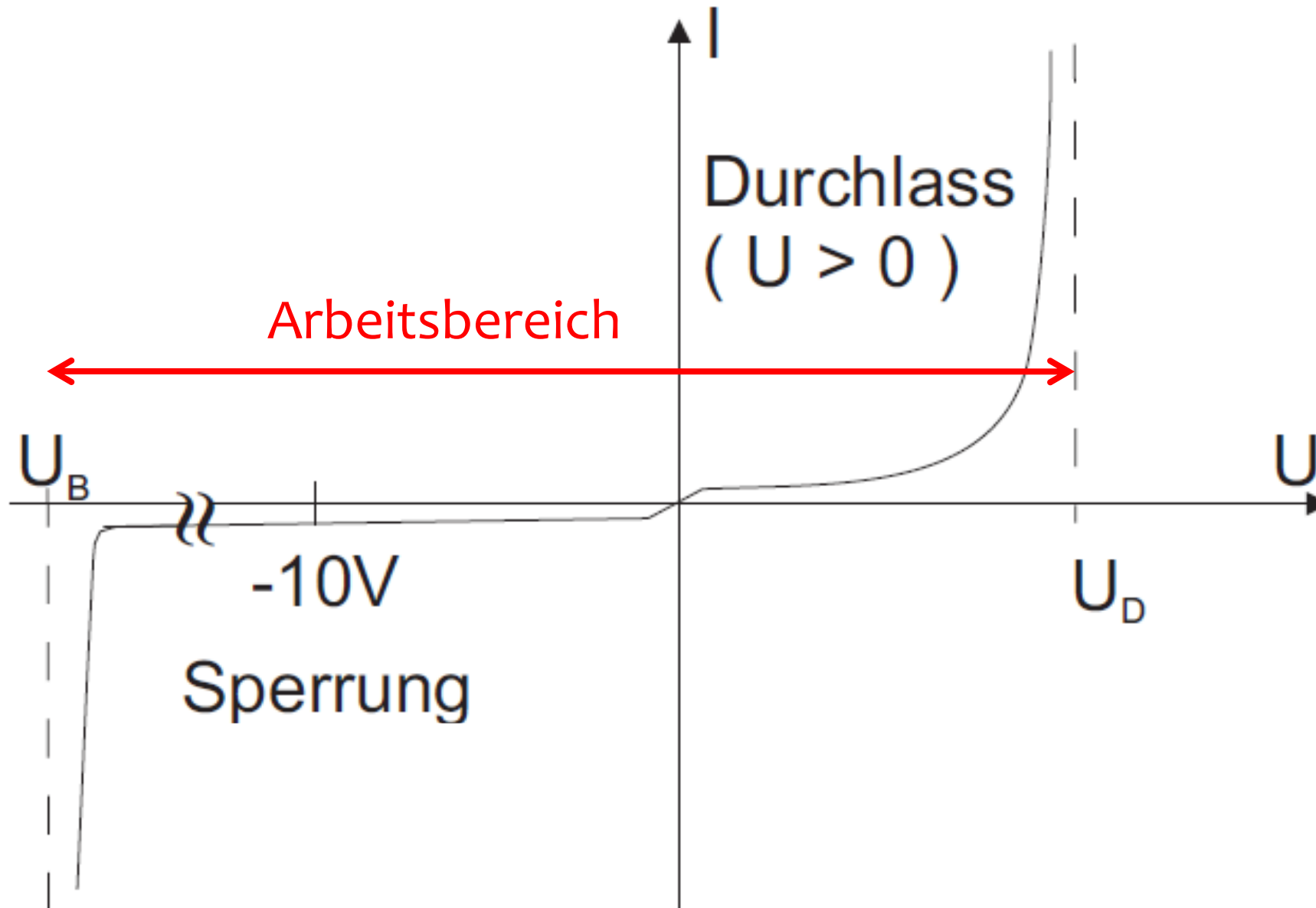




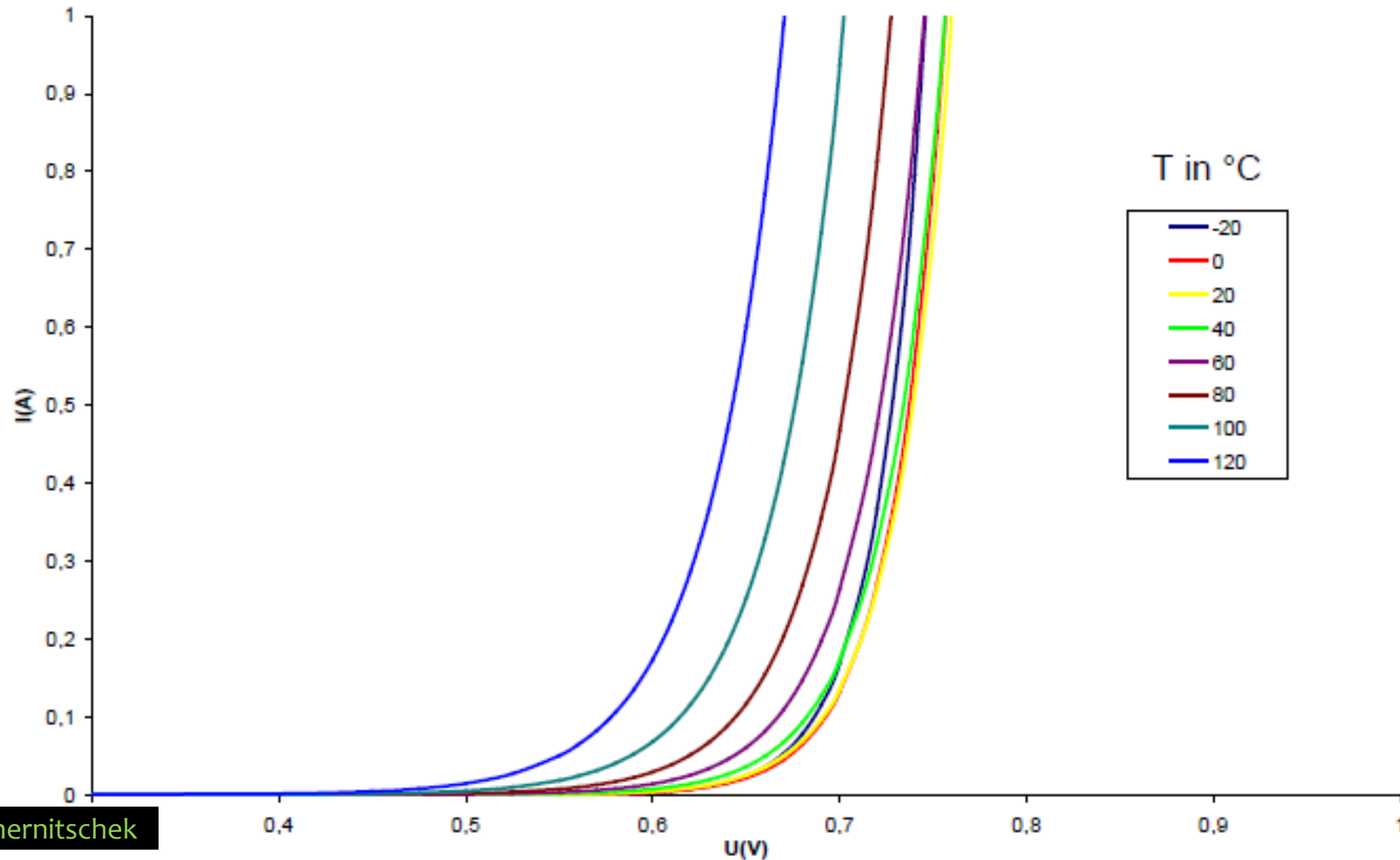


$$I_D = I_S \cdot \left(e^{\frac{U_D}{U_T}} - 1 \right), U_T = \frac{kT}{e}$$

$$\lim_{U \rightarrow -\infty} I(U) = I_S \cdot (-1)$$

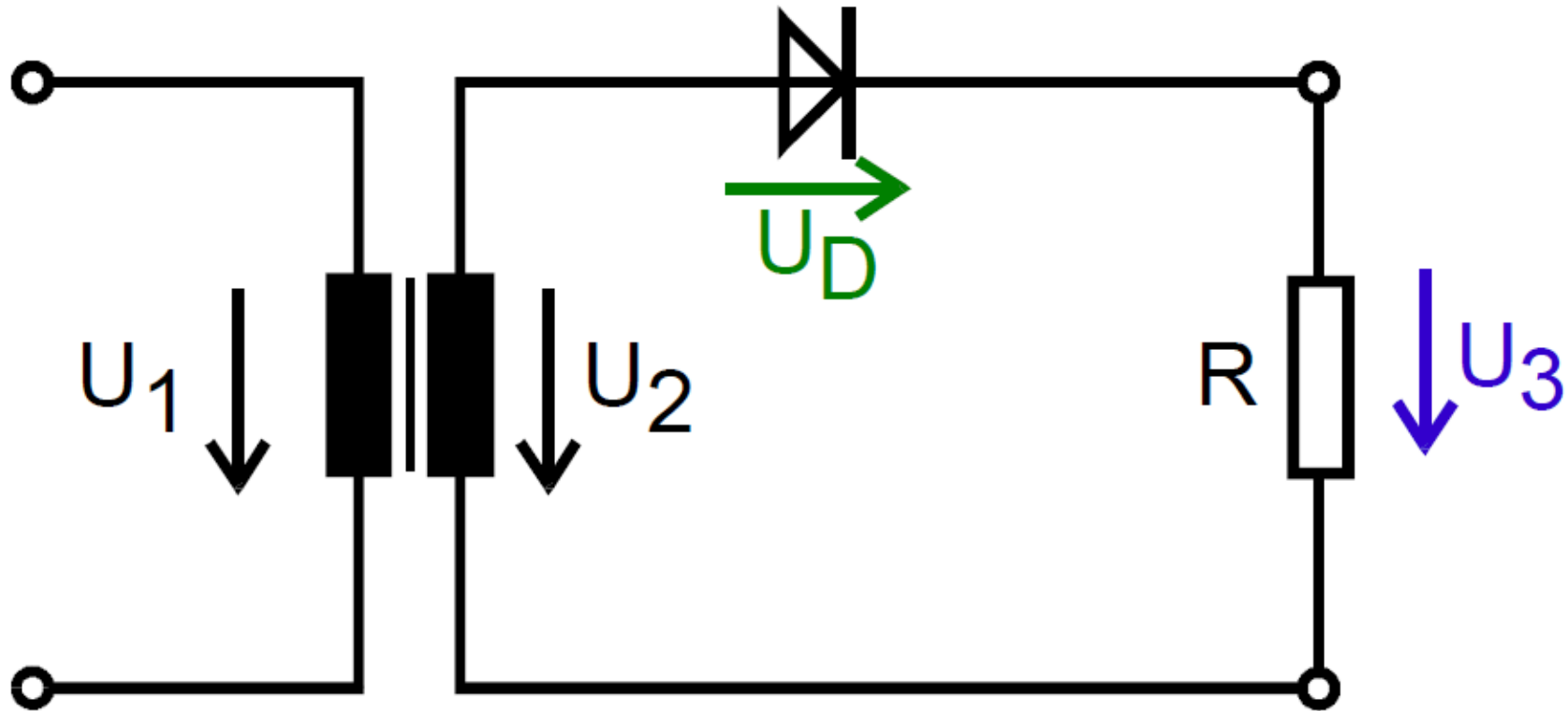


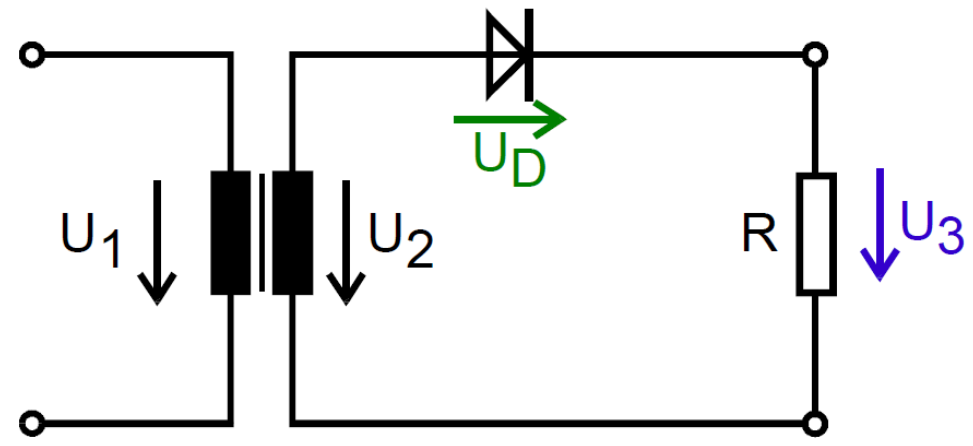
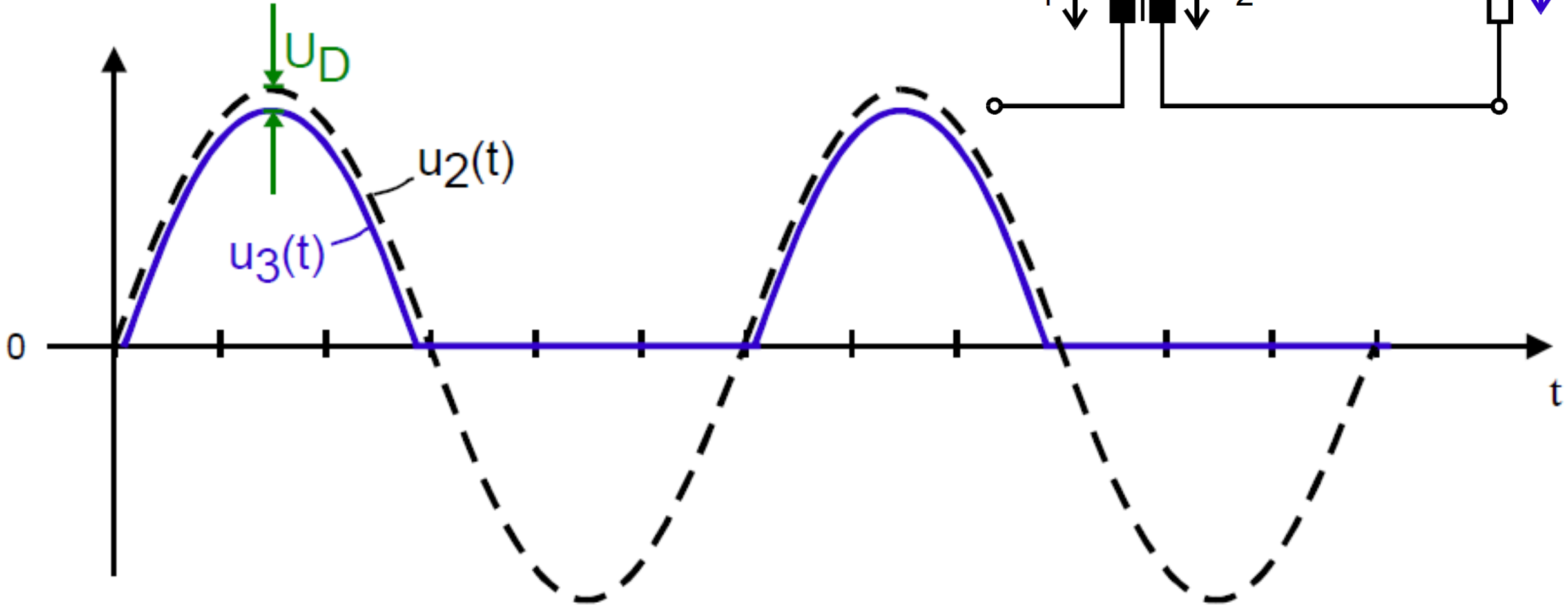
Temperaturabhängigkeit der Kennlinie



Schaltungen mit Dioden

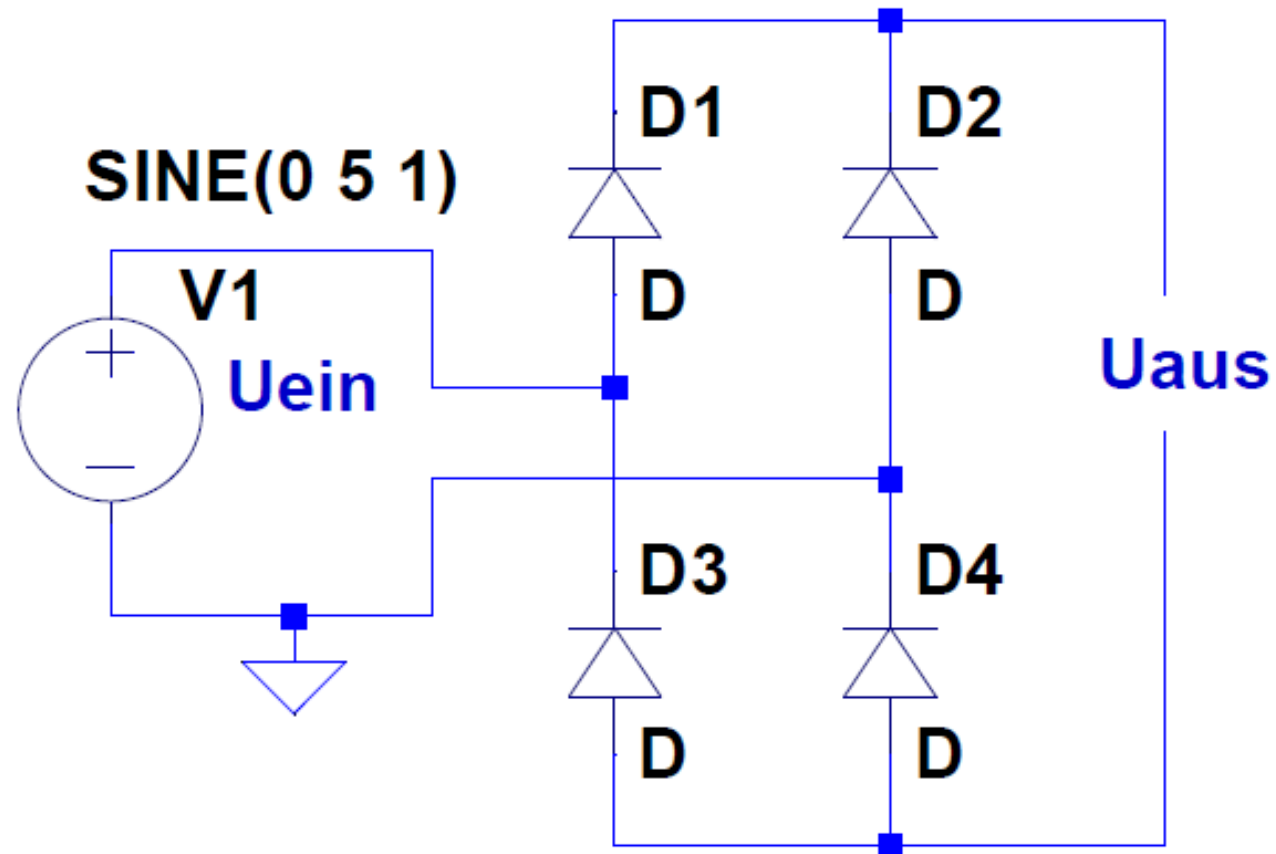
- Einweggleichrichter:

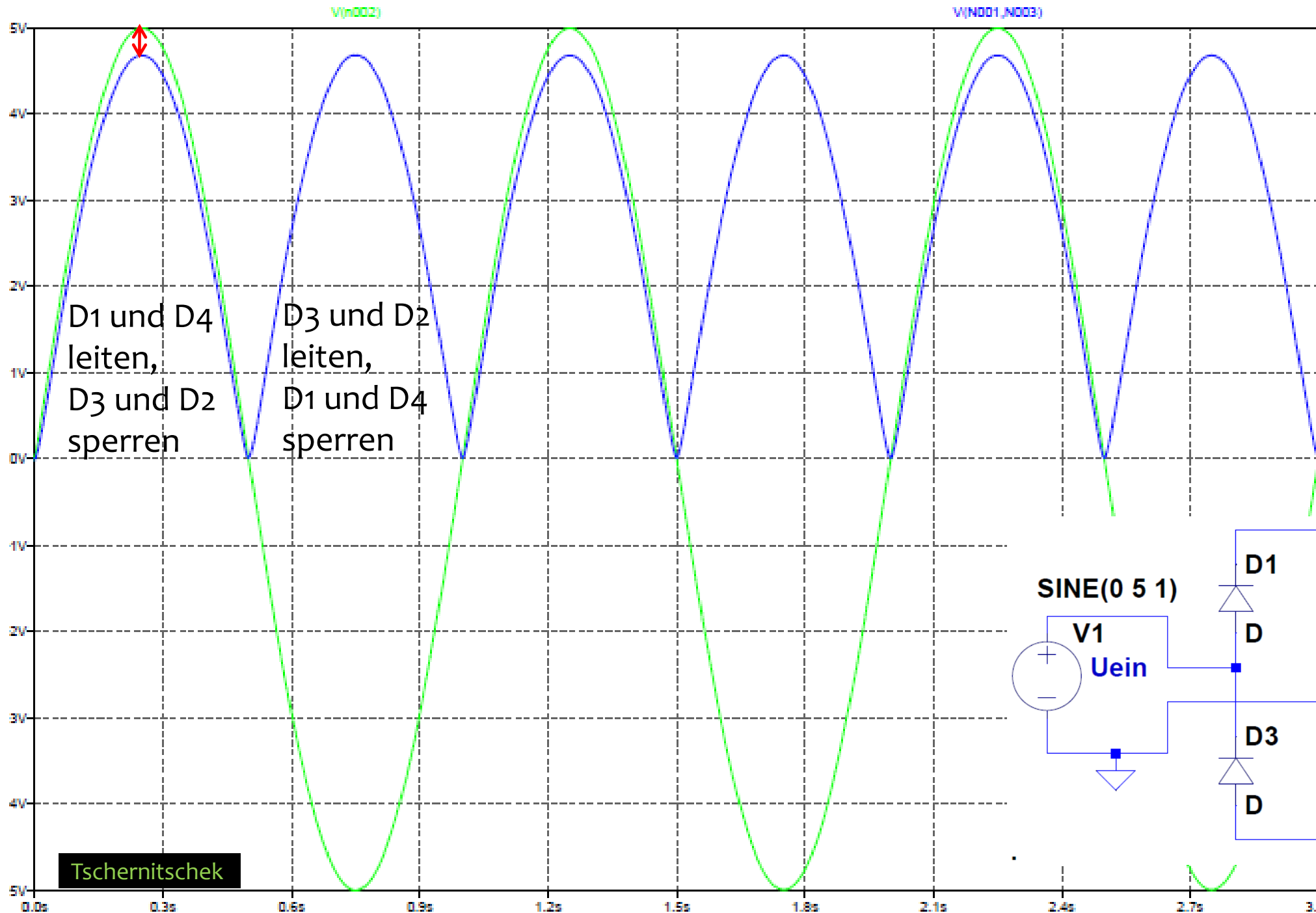




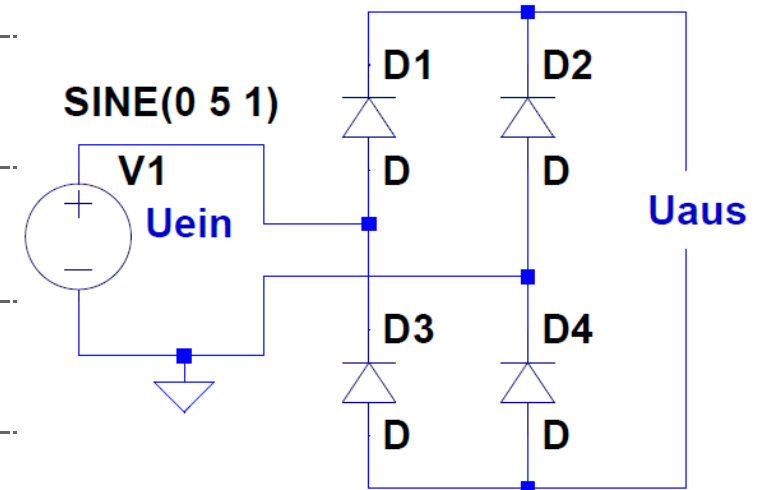
Schaltungen mit Dioden

- Brückengleichrichter (Graetz-Schaltung):



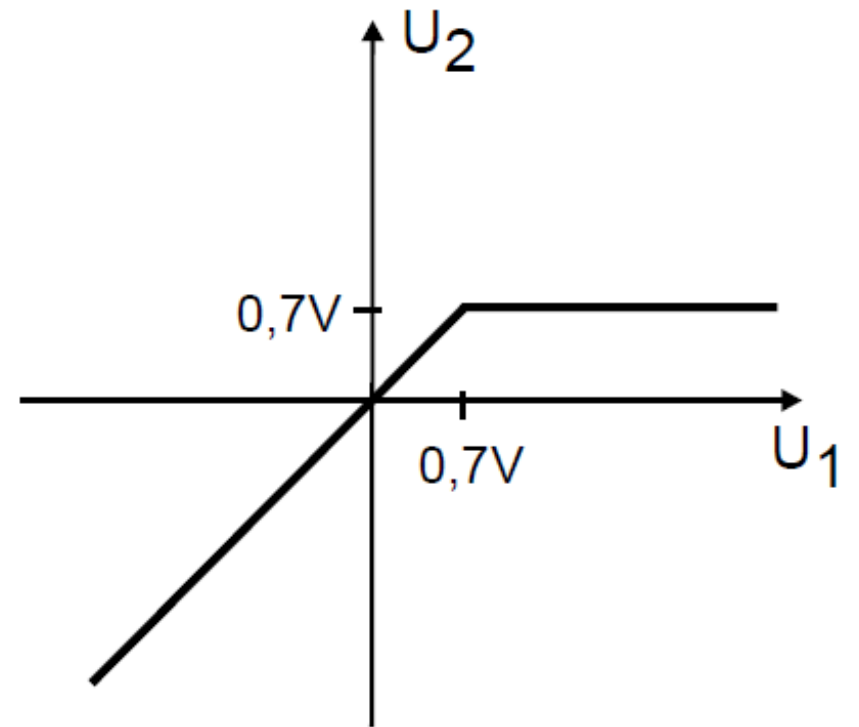
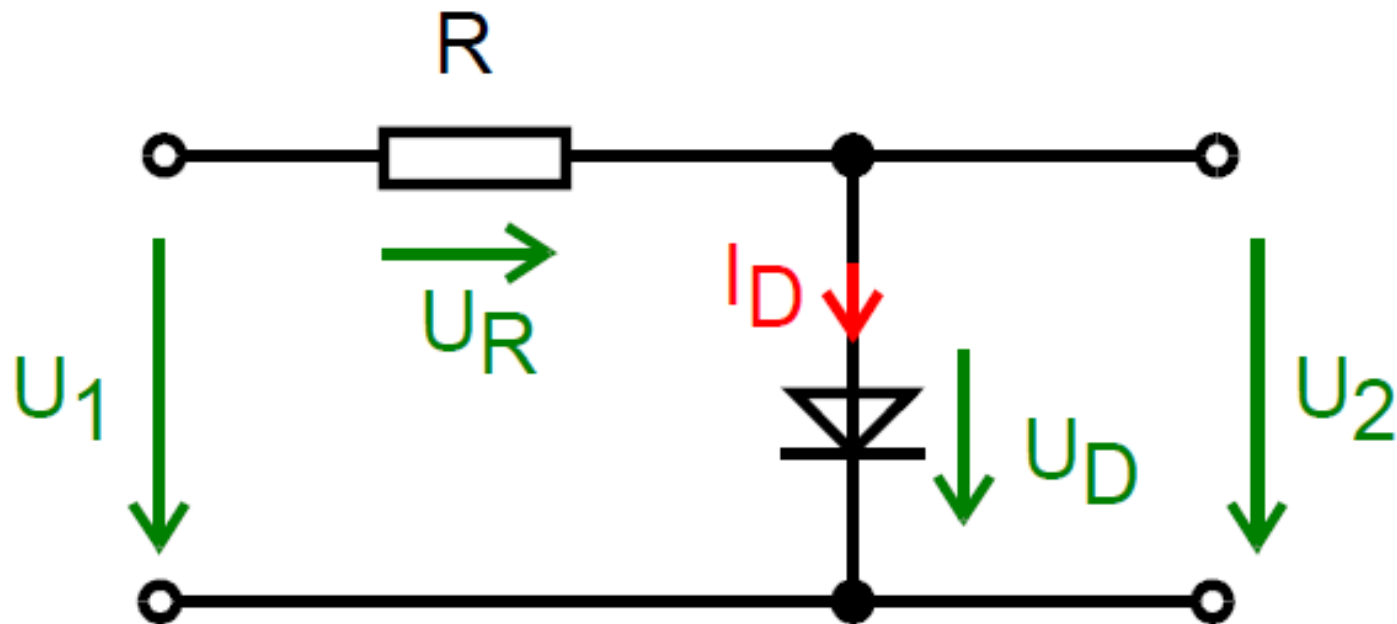


Tschernitschek



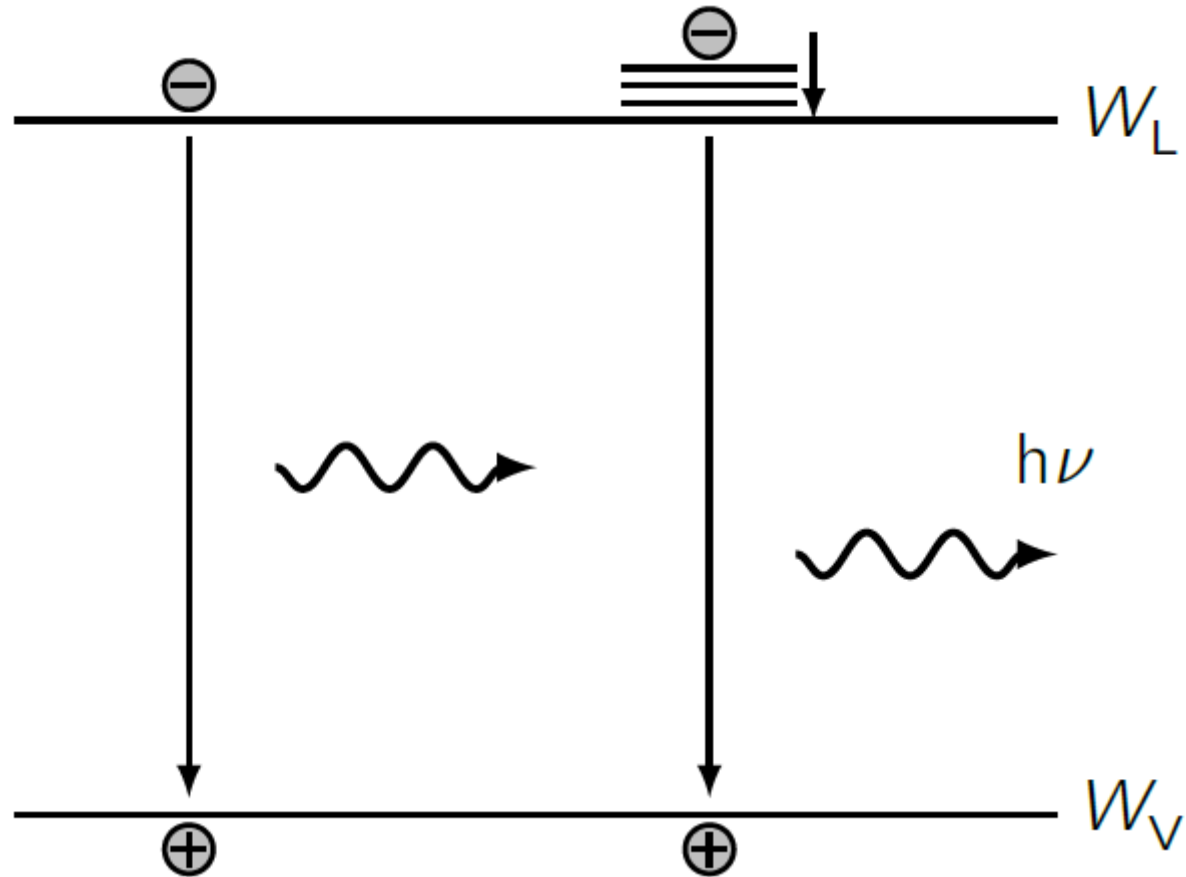
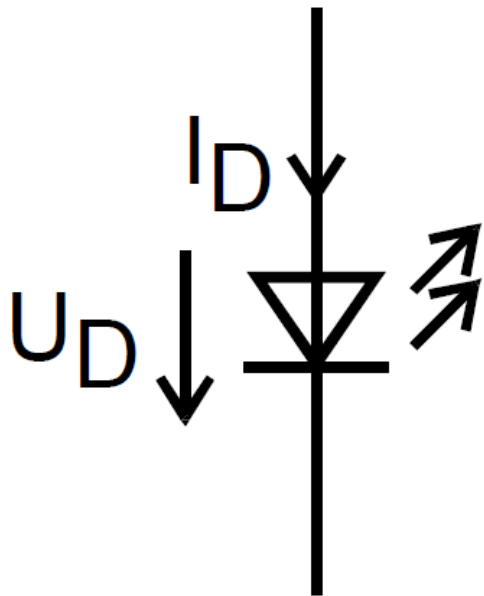
Schaltungen mit Dioden

- Begrenzerschaltungen:



Schaltungen mit Dioden

- LED:



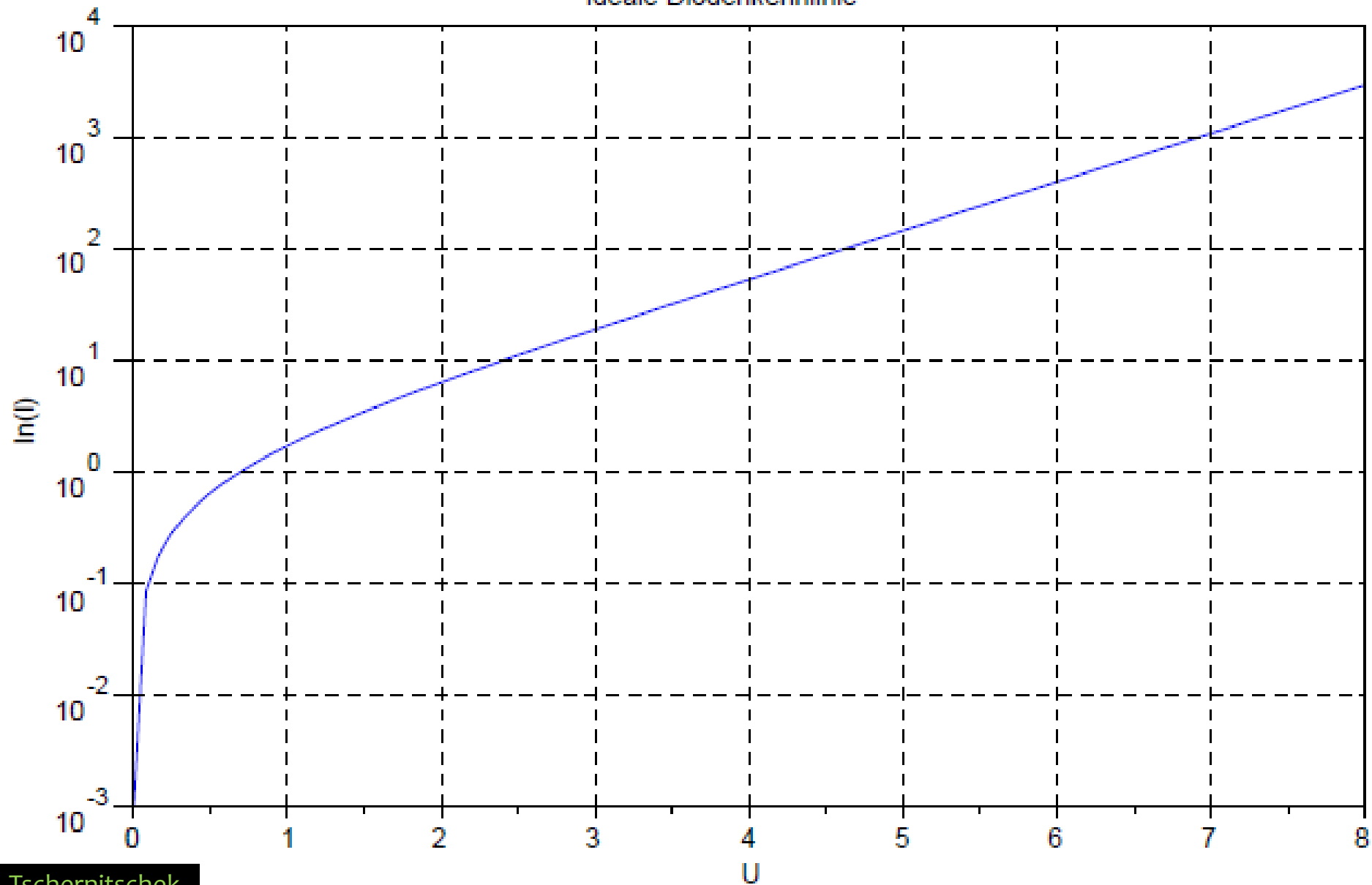
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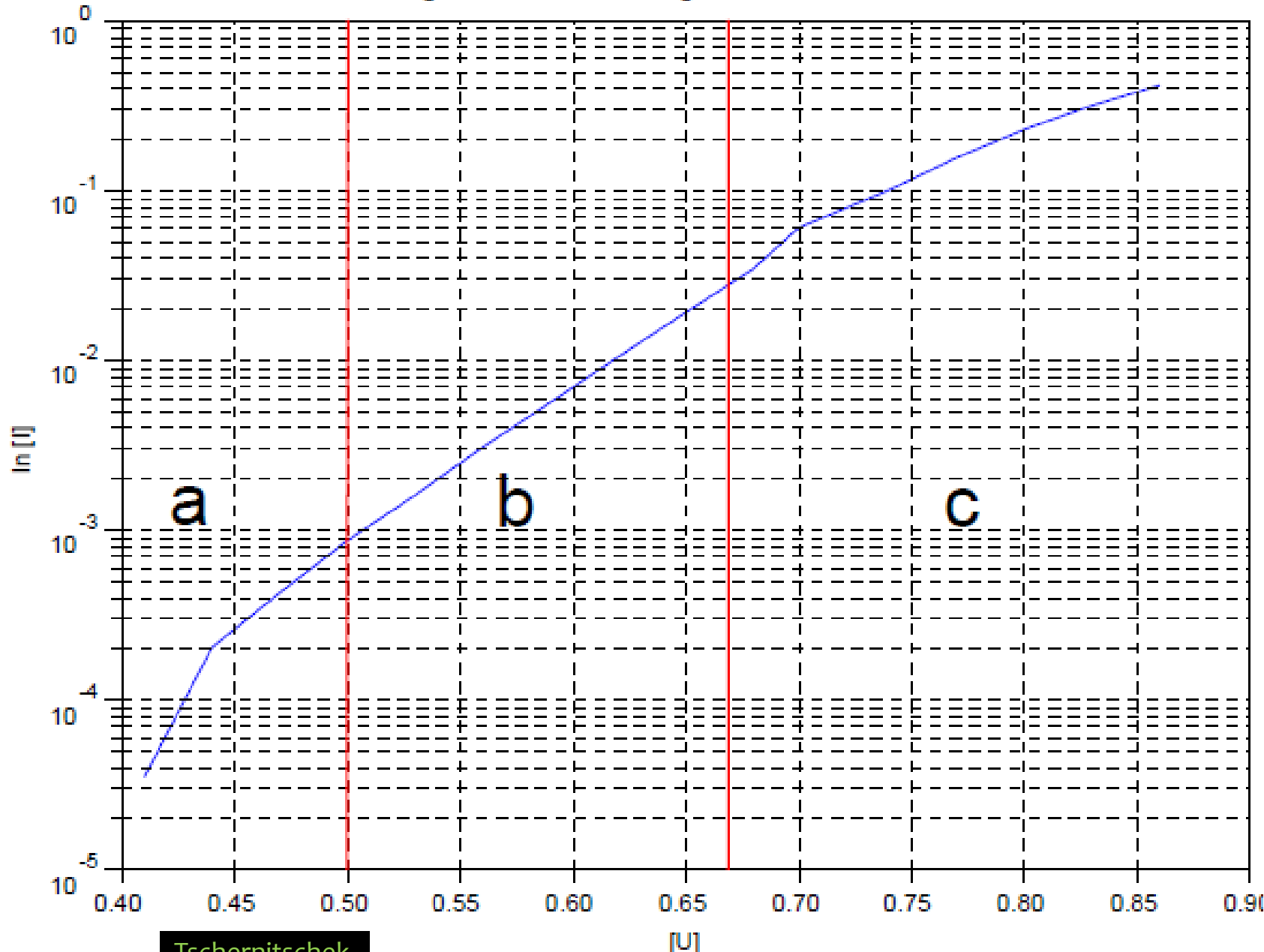
Shockley Bedingungen

- **kein Spannungsabfall über den Bahngebieten**
 - gesamter Spannungsabfall über RLZ
 - Bahngebiete widerstandslos, ideal leitend
- **keine Generation/Rekombination von Ladungsträgern in RLZ**
 - kein Verlust (in=out)
- **schwache Injektion**
 - Niveau Minoritäten trotz Injektion deutlich unter Majoritäten
- **abrupter pn-Übergang**
 - konstante Konzentration Akzeptoren /Donatoren in Bahngebieten bis zum Übergang
- **keine frei beweglichen Ladungsträger in RLZ**
 - im TG befinden sich in RLZ nur ortsfeste, positiv geladene Donator- (N_D^+) und negativ Akzeptoratome (N_A^-)

Ideale Diodenkennlinie



Halblogarithmische Darstellung Diode 1N4001 60°C



Tschernitschek

$a: I \approx e^{\frac{U}{2U_T}}$

➤ Rekombination in RLZ

$b: I \approx e^{\frac{U}{U_T}}$

➤ ideal

$c: I \approx U$

➤ Spannungsabfall über den Bahngebieten